

**'014 patent, changes in claim 21 compared to claim 1**

21. An electronic system, ~~the system~~ comprising: at least one semiconductor device, the at least one semiconductor device including: a substrate of a first doping type at a first doping level having a surface; a first active region disposed adjacent the surface of the substrate with a second doping type opposite in conductivity to the first doping type and within which transistors can be formed in the surface thereof; a second active region separate from the first active region disposed adjacent to the first active region and within which transistors can be formed in the surface thereof; transistors formed in at least one of the first active region or second active region; at least a portion of at least one of the first and second active regions having at least one graded dopant concentration to aid carrier movement from the ~~first and second active regions towards~~ surface to an area of the substrate where there are no active regions; and at least one well region adjacent to the first or second active region containing at least one graded dopant region, the graded dopant region to aid carrier movement from the surface ~~towards~~ to the area of the substrate where there are no active regions, and wherein ~~at least some of the transistors form digital logic of the semiconductor device.~~ graded dopant concentration is linear, quasilinear, error function, complementary error function, or any combination thereof.